







UNITATEA EXECUTIVA PENTRU FINANTAREA INVATAMANTULUI SUPERIOR, A CERCETARII DEZVOLTARII SI INOVARII

SUPRAMOLECULAR ORGANIC SEMICONDUCTING MATERIALS FOR OPTOELECTRONICS

Acronim: SUPRAMOL-MAT

Scientific Report STAGE 3 / 2024

Code project: PN-III-P4-PCE-2021-0906

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Objectives/2024

W3.2. The synthesis of thiophene-phenylene-azomethine (TPA) and its inclusion complexes TPA/TMS· β CD,TPA/TMS· γ CD,TPA/TMe· β CD, TPA/TMe· γ CD and TPA/CB7;

W3.3. The synthesis of polyrotaxanes (PFTPA PRs) and the reference copolymer (PFTPA): Structural characterizations and photophysics by FTIR, NMR, GPC, TGA,

DSC, ESI-MS, UV-Vis, RAMAN and TEM;

W3.4. Electrochemical and morphological properties of PFTPA PRs and PFTPA;

W3.5. Electrical conductivities of PFTPA PRs and PFTA in their undoped and doped forms;

W3.6. Surface pressure-area isotherms and BAM studies of PFTPA PRs and PFTPA at the air/water interface;

W3.7. The testing in organic electronic devices: photovoltaics (PSCs) and other organic electronic devices

<u>W3.2. - 2024</u>

The synthesis of thiophene-phenylene-azomethine (3) and its inclusion complex 3·TMe-βCD



Scheme 1. Synthetic route to the target bisazomethine 3 and its encapsulated form 3·TMe-βCD.

Structural characterization



Figure 1. FT-IR spectrum correlated with DFT calculations of 3 bisazomethine.



FIGURE 2. 1H-NMR spectrum of 3 in CDCl3.

The host-guest complexation stoichiometry



Figure 3. UV-Vis absorption titration of bisazomethine **3** monomer (1 μ M solution in DCM) with increasing the concentration of TMe- β CD. The nonlinear fitting based on the UV-Vis absorption change assuming a 1:1 binding model, from which the association constant was derived.



DFT computations for exploring electronic structure



Figure 5. Molecular insights of compound **3**: Optimized geometry (conformation) by DFT method (a); distribution of partial atomic charges (Mulliken) and dipole moment value (b); electrostatic potential (c), represented as a mapped surface surrounding molecule 3, highlighting electrophilic attack sites (E+) and nucleophilic attack sites (Nu–); computation conducted at the APFD/6-311G(2d,p) theory level.

Figure 6. Frontier molecular orbital patterns (HOMO & LUMO) and corresponding band-gap energy value for compound **3**.

Molecular docking simulation



Figure 8. Frontier molecular orbital patterns (HOMO and LUMO) and corresponding bandgap energy value for the host-guest complex **3·TMe-βCD**.

The surface morphology



Figure 10. CV curves of 3 (red) and 3·TMe-βCD (blue) in the anodic region, registered at 50 mV·s-1.

Figure 11. Repetitive 10 CV scans of 3 in the anodic region registered at 50 mV·s-1.

red.

1.0

1.2

1.4

Surface pressure-area isotherms and BAM studies of 3 and 3·TMe-βCD monolayers



Figure 12. Compression isotherms and BAM images (600 μ m x 600 μ m) of **3** (black frame) and **3·TMe-BCD** (red frame) monolayers at 2 mN·m-1 and in the collapsed phases.

W3.3. Sinteza polirotaxanilor si a polimerului de referinta



Scheme 2. Synthesis protocol of **4·TMe-βCD** and **4** bisazomethine-based copolymers.

Structural characterizations



8.5 8.0 7.5 7.0

6.5

6.0 5.5 5.0 4.5 4.0

Figure 14. 1H-NMR spectra of the $4 \cdot \text{TMe-}\beta\text{CD}$ (top) and 4 (bottom) in CDCl3.

3.5 3.0 2.5 2.0 1.5 1.0 0.5 0.0

The surface morphology



Figure 15. AFM images of **1** (a,b) and **4** (c,d) thin films prepared by drop-casting from THF solution in concentrated and dilute regimes, respectively.

Figure 16. AFM images of **1·TMe-βCD** (a,b) and **4·TMe-βCD** (c,d) thin films prepared by drop-casting from THF solution in concentrated and dilute regime, respectively.

Optical Properties



Figure 17. UV-Vis absorption, fluorescence and phosphorescence spectra of **4** (a) and **4**·**TMe**-**\betaCD** (b) and fluorescence spectra of **4** and **4**·**TMe**- β CD (c) at λ ex = 375.

Table 1. Emission lifetimes (τ) and chi-squared $(\chi 2)$ determined by nanosecond transient absorption, and quantum yields for fluorescence (Φ FL) and phosphorescence (Φ Ph) of the synthesized Schiff bases **4** and **4-TMe-BCD** in ACN.



Figure 18. Nanosecond transient absorption maps of **4** (a) and **4**·**TMe**-**\betaCD** (b) in ACN (λ ex = 375 nm) (the black circle shows the isosbestic points).

Electrochemical properties



Figure 19. Cyclic voltammograms of fresh films of **4** (a) and **4**·**TMe**-**\betaCD** (b) at different scan rates, in the anodic region (inset: enlarged view of the CV curve of **4**·**TMe**-**\betaCD** at 10 mV·s-1).



Figure 20. Cyclic voltammograms of **4** and **4·TMe-βCD** at 50 mV·s-1 (left) and comparative CV curves of **4·TMe-βCD** at 10 and 50 mV·s-1 (right) in the cathodic region.

Electrical properties



Figure 21. Variation of dielectric constant as a function of frequency of **4** and **4·TMe-βCD**.

Table 2. Electrical conductivities of **4** and **4**•**TMe**-**βCD**.

Sample	σ (S∙cm⁻¹) ª)	σ (S∙cm⁻¹) ^{b)}	σ (S∙cm⁻ ¹) ^{c)}
4	2.1 x 10 ⁻¹¹	7.3 x 10 ⁻¹⁰	8.5 x 10 ⁻⁷
4·TMe-βCD	6.2 x 10 ⁻¹²	8.1 x 10 ⁻¹¹	2.2×10^{-8}
		DDC meethed	

a)Conductivity measured by BDS method of undoped pellets; b)Conductivity measured by the four-point method of undoped pellets; c) Conductivity measured by the fourpoint method of iodine-doped pellets.

Figure 22. The variation of σ with f under alternating electrical field of **4** and **4**·**TMe**-**\betaCD** samples.

Surface pressure-area isotherms and BAM studies of Langmuir monolayers



Figure 23. Compression isotherms and BAM images (600 μ m x 600 μ m) of **4** (black frame) and **4·TMe-BCD** (blue frame) monolayers at 2 mN·m-1 and in the collapsed phases.

Diode fabrication



Manufactured prototype diode structure (a) and schematic diagram used to connect the source measurement unit to the diode in a 4-wire configuration (b).

This value is quite close to conventional diodes and similar to the reported values for hybrid diodes found in the literature

Measured current-voltage characteristic of the eGaIn/4TMe- β CD/ZnO/AI:ZnO manufactured diode: a) the nonlinear currentvoltage characteristic I=f(U); and b) the representation of the linear region from the semilogarithmic plot.

Preliminarily photovoltaic results of 4·TMeβCD and 4



Figure 23. Energy level alignment of different device components.



Dissemination - 2024

ISI published papers: 3

- 1. B. Hajduk , P. Jarka, H. Bednarski , H. Janeczek , P. Kumari , A. Farcas, Thermal transitions and structural characteristics of poly(3,4-ethylenedioxythiophene/cucurbit[7]uril) polypseudorotaxane and polyrotaxane thin films, Materials 2024, 17, 1318. https://doi.org/10.3390/ma17061318
- 2. A.-M. Resmeriţă, M. Asăndulesa, A. Farcaş, Composite materials based on slide-ring polyrotaxane structures for optoelectronics, J. Polym. Sci. 2024, 1-11. https://doi.org/10.1002/pol.20240285

Submmited: 1

1. A.-M. Resmerita, C. Cojocaru, M.-D. Damaceanua, M. Balan-Porcarasu, S. Shova, A. El Haitami, A. Farcas, A thiophene-based bisazomethine and its inclusion complex with permethylated β-cyclodextrin: Exploring structural characteristics and computational chemistry models (DYPI-D-24-00645R1)

Plenary conferences: 3

 A. Farcaş, Supramolecular encapsulation of semiconductors as a promising approach to organic electronic materials, Semiconductor Materials Forum -SEMICONFORUM2024, 11-15 august/2024, Madrid-Spania. https://www.continuumforums.com/2024/semiconforum
A. Farcaş, A.-M. Resmeriţă, SUPRAMOLECULAR SEMICONDUCTORS TOWARD ORGANIC ELECTRONIC MATERIALS, PolyChar World Forum on Advanced Materials 30th Edition, September 11 - 13, 2024, Iasi -Romania
A. Farcaş, SUPRAMOLECULAR ORGANIC SEMICONDUCTORS: RECENT ADVANCES AND PERSPECTIVES FOR OPTOELECTRONICS, CNCHIM2024 NATIONAL CONFERENCE OF CHEMISTRY. XXXVII EDITION, September 25-27, 2024, Targoviste-Romania

Other:

1. A. Farcaş - Program Committee, KEYNOTE SPEAKER at the Semiconductor Materials Forum - SEMICONFORUM2024, 11-15 august/2024, Madrid-Spania. https://www.continuumforums.com/2024/semiconforum